

ELECTRONIC INFORMATION DISCLOSURE STATEMENT

Electronic Version v18
Stylesheet Version v18.0

Title of Invention

NON-VOLATILE MEMORY ARRAY WITH SIMULTANEOUS WRITE AND ERASE FEATURE

Application Number:

10/773059

Confirmation Number:

5441

First Named Applicant:

Bohumil Lojek

Attorney Docket Number: ATM-275

IM-2/5

Art Unit:

-2818- 2824

Search string:

(4334292 or 4432075 or 4821236 or 4890259

or 5126967 or 5990512 or 6125053).pn.

US Patent Documents

Note: Applicant is not required to submit a paper copy of cited US Patent Documents

init	Cite.No.	Patent No.	Date	Patentee	Kind	Class	Subclass
145	1	4334292	1982-06-08	Harish N Kotecha	A1	365	182
145	2	4432075	1984-02-14	Boaz Eitan	A1	365	185
143	3	4821236	1989-04-11	Yutaka Hayashi et al.	A1	365	185
465	4	4890259	1989-12-26	Richard T. Simko	A1	365	45
145	5	5126967	1992-06-30	Richard Simko	A1	365	45
465	6	5990512	1999-11-23	Christopher J. Diorio et al.	A1 ·	257	314
455	7	6125053	2000-09-26	Christopher J. Diorio et al.	A1	365	185.03

Signature

·	Examiner Name	Date			
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FORM	FORM PTO-1449				Atty. Dock ATM-275	y. Docket No. Serial No. 10/773,059				
LIST OF PRIOR ART CITED BY APPLICANT				Applicants: Bohumil Lojek						
	CITED BY APPLICANT MAIL TRADEMARK				Filing Date: Feb. 4, 2004			Group: 2818		
				PATEN	T DOCUMENTS					
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AGS	AO	B. Eitan et al. (School of Applied Science and Technology, The Hebrew University of Jerusalem, Jerusalem, Israel), Impact Ionization at Very Low Voltages in Silicon, J. Appl. Phys. 53(2), February 1982, pp. 1244-1247.								
	AP									
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